SiC Schottky Barrier Diodes

SCS112AG

[Product description]

Switching loss reduced, enabling high-speed switching . (2-pin package)

Features

- Shorter recovery time
- Reduced temperature dependence
- High-speed switching possible

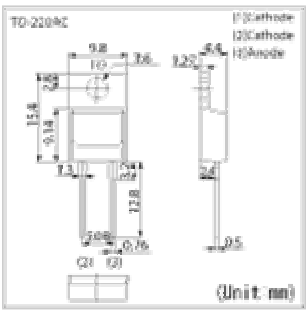
Product specifications

Absolute maximum ratings (Ta=25ºC)		
Rated parameters	Standard value	Conditions
Repetitive peak reverse voltage V_{RM}(V)	600	
Reverse voltage(DC) V_R(V)	600	
Average rectified forward current I_O(A)	12	
Forward current surge peak I_{FSM}(A)	48	60Hz/1cyc
Junction temperature Tj(ºC)	150	
Storage temperature Tstg(ºC)	-55 to +150	

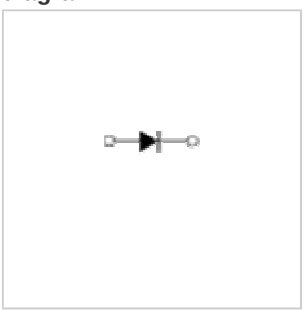
Outline

9.8x15.4(t=4.4)

Dimensions



Equivalent circuit diagram



*The contents described here are just outline for introduction.

Please obtain the specification sheets from us for thorough check before use.

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